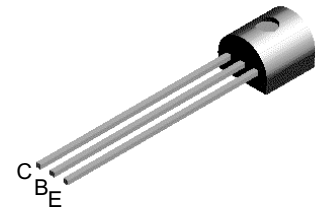


**S9015-B**  
**S9015-C**  
**S9015-D**

**Features**

- TO-92 Plastic-Encapsulate Transistors
- Capable of 0.45Watts( $T_{amb}=25^{\circ}C$ ) of Power Dissipation.
- Collector-current -0.1A
- Collector-base Voltage -50V
- Operating and storage junction temperature range:  $-55^{\circ}C$  to  $+150^{\circ}C$
- Marking: S9015
- Lead Free Finish/RoHS Compliant ("P" Suffix designates RoHS Compliant. See ordering information)
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1



**Electrical Characteristics @ 25°C Unless Otherwise Specified**

Symbol	Parameter	Min	Max	Units
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**OFF CHARACTERISTICS**

$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ( $I_C = -100\mu A, I_E = 0$ )	-50	---	Vdc
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ( $I_C = -1.0mA, I_B = 0$ )	-45	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ( $I_E = -100\mu A, I_C = 0$ )	-5.0	---	Vdc
$I_{CBO}$	Collector Cutoff Current ( $V_{CB} = -50Vdc, I_E = 0$ )	---	-0.05	$\mu A$
$I_{EBO}$	Emitter Cutoff Current ( $V_{EB} = -5.0Vdc, I_C = 0$ )	---	-0.05	$\mu A$

**ON CHARACTERISTICS**

$h_{FE}$	DC Current Gain ( $I_C = -1.0mA, V_{CE} = -5.0Vdc$ )	60	1000	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ( $I_C = -100mA, I_B = -10mA$ )	---	-0.3	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ( $I_C = -100mA, I_B = -10mA$ )	---	-1.0	Vdc

**SMALL-SIGNAL CHARACTERISTICS**

$f_T$	Transistor Frequency ( $I_C = -10mA, V_{CE} = -5.0Vdc, f = 30MHz$ )	150	---	MHz
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**CLASSIFICATION OF  $h_{FE}$**

Rank	B	C	D
Range	100-300	200-600	400-1000

